



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	260mA
$R_{DS(ON)}$ (at $V_{GS}=10V$)	2.5ohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	3.0ohm
Gate-Source ESD Rating Up to 2KV (HBM)	

General Description

Trench Power MV MOSFET technology
Voltage controlled small signal switch
Low input Capacitance
Fast Switching Speed
Low Input / Output Leakage
Moisture Sensitivity Level 3
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

Battery operated systems
Solid-state relays
Direct logic-level interface TTL/CMOS

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)



2N7002KCL3

Electrical Characteristics (T_j=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250				



Typical Performance Characteristics

Figure1. Output Characteristics

Figure2. Transfer Characteristics



Figure7. On-Resistance vs V_{GS}

Figure8. Threshold Voltage vs Temperature



DFN1006-3L Package information



